Supporting Information

Unraveling the growth mechanism of W₁₈O₄₉ nanowires on W surfaces

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S.1: Experimental setup



Figure S1. The schematic representation of the experimental setup for the heat treatment performed in the current work.

S.2: Characterization of precursor W



Figure S2. a) XRD profile of the precursor W powder and b) its SEM micrograph revealing irregular particle nature.

S.3: Appearance of the W powder obtained after thermal treatments



Figure S3. The appearance of final products after thermal treatments. a) W heat-treated at 650 °C/1h in $H_2O(v)$ atmosphere showing the bluish brown color. b) the sample heat-treated at 800 °C/1h showing lucent blue color.



S.4: Results of the intermediate thermal treatment at 450°C/1h

Figure S4. a) XRD and b) SEM micrographs of the W thermally treated at 450° C/1h under Ar+H₂O(ν) atmosphere.

S.5: Dimensions of W₁₈O₄₉ NWs

The diameters and the lengths of the NWs are measured from the FESEM micrographs using ImageJ software (Ver $1.8.0_{172}$). The statistics of the diameters obtained were varied from ~30 nm to ~400 nm. However, the NWs with a diameter <50 nm were not well resolved in the microscopy. The microscopic data is mostly dominated by the NWs with >150 nm. The average diameter of the NWs from the obtained data is calculated as 140 ± 90 nm, as shown in **Figure S5**. Whereas the average length of the well resolved NWs was measured to be 6.5 ± 1.5 µm. These statistics are compared with the other results from the literature where the thermal annealing routs were used for the synthesis.



Figure S5. The size distributions of a) diameter and b) lengths of $W_{18}O_{49}$ NWs. The statistics were obtained from FESEM micrographs.

An attempt has been made to compare the product obtained in the current work with the same material reported in the literature. In this view, the details of the $W_{18}O_{49}$ 1d nanostructures synthesized via thermal annealing routes are collected. A comparison table consisting of precursor, temperature, furnace conditions, i.e., atmosphere, time, resultant phase, morphology, growth, and their dimensions, is made as shown in **Table S.1**.

Precursor	Temp °C	Atmosphere	Time	Resultant phase & morphology	esultant phase & Growth morphology mechanism		Dia	Length	Ref.
W	800	$H_2O(v)$	1 h	W ₁₈ O ₄₉ NWs	SS $(H_2O(v) \text{ reaction})$	Very high	30-400nm 140 nm (avg)	6.5 µm	C.W.
W	650	$H_2O(v)$	1 h	W ₁₈ O ₄₉ NWs	- induced)	Less	-	-	C.W.
W tip	700	Ar (O ₂ leakage)	10 min	W ₁₈ O ₄₉ NWs	VS (expected)	Less	10-30 nm	300 nm	1
W plate	700	Ar (O ₂ leakage)	1 & 3 h	W ₁₈ O ₄₉ NWs	VS (expected)	Very less	-	500 nm & 1.6 μm	1
W powder (0.6 - 1 µm)	800		20,40 &120 min	W ₁₈ O ₄₉ NNs		Very high	20-400 nm	10-20 μm	2
100 mesh W powder	800	-	40 min	W ₁₈ O ₄₉ NNs/NRs	H ₂ O(v) reaction induced	Moderate	0.5-1 μm	10-20 μm	2
100 mesh W powder	1000	$\operatorname{Ar+H_2O}(v)$	1 h	W18O49 MBs		High	-	~ 1mm	2
W foil (0.5mm thick)	800	-	40 min	W ₁₈ O ₄₉ NNs	_	High	-	-	2
W wire (0.25 mm dia)	800	-	40 min	W ₁₈ O ₄₉ NN bushes		High	-		2
W powders	1400 & 1300	Vacuum ~7.7 Pa, and Ar	0.5 h	W ₁₈ O ₄₉ NTs	VS (expected)	High	-	~35 µm	3
Array of tungsten filaments (0.2 mm diameter)	1150	0.6 Torrr & Ar (O ₂ leakage also)	0.5 h	W ₁₈ O ₄₉ NWs	VS	High	100 nm	500 μm	4
	1200		0.5 h	W ₁₈ O ₄₉ NBs	VS	High	200 nm, (30 nm each)		4
W powder	650	20 Torr	2 h	W ₁₈ O ₄₉ NWs	VS	Less	10-50 nm	0.5 – 1.5 μm	5
W powder (0.2 µm)	600	$Ar + H_2O(v)$	0.5 h	W ₁₈ O ₄₉ NWs	H ₂ O(v) reaction induced	Moderate	20-50 nm	Several µm	6
WO ₃ powder	900 to 1000	5-7 mTorr, and ~0.13 sccm air	3 h	W ₁₈ O ₄₉ NWs	VS	High	10-20 nm	Few µm	7
Sputtered tungsten film	800	0.04-0.05 Pa, and 1-1.5 sccm O ₂	0	W ₁₈ O ₄₉ NWs	Solid phase	Less	-	-	8
W filament		0.8 Torr, and 200 sccm Ar	0.5 h	W ₁₈ O ₄₉ NWs	VS	High	Several nm	Several µm	4,9
WO ₃ powder	950,	0.1 and 1 Torr,	No soaking	W ₁₈ O ₄₉ NWs	Thermal	Less	90-1000 nm	> 1 µm	10

Table S1. The comparison table of $W_{18}O_{49}$ 1*d* nanostructures obtained via thermal annealing routes.

	1000	and Ar			evaporation/VS				
	and								
	1050								
Milled W	1400	Ar	-	W ₁₈ O ₄₉ NWs	Thermal evaporation/VS	Less	30-50 nm	700 nm	11
Sputtered tungsten film (150 nm thick)	650	15 Pa, Ar, and O ₂ (0.1 sccm)	1 h	W ₁₈ O ₄₉ NWs	Thermal Oxidative	Moderate	10-20 nm	0.5 – 1 μm	12
Amorphous W film	650	PLD (40 & 50 Pa)	10 h	W ₁₈ O ₄₉ NWs	Vacuum annealing	Less	20-40 nm	0.85-0.36 μm	13
WO ₃ powder covered with W sheet	1000	100 m Torr,	1 h	WO _{2.9} NRs	VS (expected)	Moderate	80-400 nm	2-3 µm	14
W powder	1100	10 Pa, Ar (100 sccm) + O ₂ (1 sccm)	1-20 min	W ₁₈ O ₄₉ NWs	VS	Moderate	-	-	15
W Coin	1400	Ar (10 sccm)	10 h	W ₁₈ O ₄₉ MRs	Thermal oxidative	Moderate	0.1 to few µm	Few µm	16
WO ₃ Powder	1100	Ar and Sulphur at upstream	1 h	W ₁₈ O ₄₉ MRs	VS	High/Mode rate	Few µm	Few µm	17,18
Sputtered W films	550	Ar	1 h	W ₁₈ O ₄₉ NWs	Thermal oxidative	Moderate	10-40 nm	400 nm	19

C.W.- current work, NWs- nanowires, NRs- nanorods, NBs- nanobundles, NNs- nanoneedles, MRs- microrods, MBs- microbundles, SS- solid solid, VS- vapor solid

S.6: W-O-H phase diagram

The W-O-H phase diagram is adapted from the literature.^{20,21} The original version of the $p[H_2]$

diagram consists of only X and Y-axis drawn as $10^3 \text{ T}^{-1}(\text{K}) \text{ Vs} \overline{p[H_2O]}$. To improve the understandability, the diagram is implemented or redrawn here as a new figure with more elaboration in **Figure S6**. For a better understanding, a top X-axis showing the temperature in °C is added. The values of the same were calculated from the $10^3 \text{ T}^{-1}(\text{K})$ value of the bottom X-axis. Similarly, a new right Y-axis with %H₂O values, which were calculated from the $p[H_2]$

 $\overline{p[H_2O]}$ values of left Y-axis. Additionally, the crystal structures of the phases were given in their corresponding regions for the crystallographic representation.



Figure S6. The equilibrium phase diagram showing the stability regions of tungsten oxides with respect to the $%H_2O$ and temperature. The phase diagram is redrawn as reported elsewhere.^{20,21}

S.7: XPS



Figure S7. The XPS full survey of W, W@450°C, and W@650°C.

The binding energies corresponding to each peak obtained from the W 4f and O 1s spectra of all samples are tabulated in **Table S2**. Also, the percentages of the oxidation states were estimated using the area of peaks obtained after deconvolution.

Table S2.	XPS	peak	positions	of	the	W	4f	spectra	of	W,	W@450°C,	W@650°C,	and
W@800°C													

W

Peak	W5p _{3/2}	W ⁶⁺ (W4f _{5/2})	W ⁶⁺ (W4f _{7/2})	W ⁵⁺	W(W4f _{5/2})	W(W4f _{7/2})
Position	41.63	37.73	35.63	-	33.4	31.28
Area	2333.61	78900.06	103843.3	-	58096.8	60691.61
%		W ⁶⁺ = 60.14		$W^{5+} = 0$	W = 39.09	

W@450°C

%		W ⁶⁺ = 68.62			W ⁵⁺ =18.0	7	W = 11.14		
Area	4318.76	1230.34	63760.04	71625.91	7575.27	28397.68	4284.37	2706.68	15192.95
Position	41.459	39.31	37.828	35.77	36.763	34.32	33.601	32.235	31.47

W@650°C

%		W ⁶⁺ = 61.18	W ⁵⁺ = 31.5	9	W = 1.32		
Area	13471.89	65992.42	73581.45	12993.46	59064.54	-	3013.02
Position	41.146	38.073	36.119	37.652	34.953	-	31.646

W@800°C

Position	40.479	37.669	37.497	35.444	36.368	34.073	-	-
Area	29440.28	78825.09	71701.22	129195.90	63464.28	104525.10	-	-
%		W ⁶⁺ = 58.62			W ⁵⁺ = 35.20		W = 0	

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